



AS098Q1200W



TECHNICAL DATA

High Power Stacked Infrared Laser Diode Array

Features

- Output Power: 1200 W qCW
- 920-980 nm Emission Wavelength
- Spectral Width: ≤ 4 nm
- High Reliability, High Efficiency
- QCW stack can be designed according to the customer of non-standard products heat sink package

Applications

- Laser Pumping
- Medical Usage
- High power laser diode applications

Specifications (25°C)

Item	Symbol	Value	Unit
Optical Specifications			
qCW Output Power	P_O	1200	W
qCW Output Power / Bar	P_S	60	W
Array Length	L	10	mm
Center Wavelength	λ_C	920-980	nm
Wavelength Tolerance		± 5	nm
Spectral Width	$\Delta\lambda$	≤ 4	nm
Package Style		Micro Channel	
Bar Length		0.4	mm
Number of Bars		20	
Wavelength Temperature Coefficient		0.3	nm/°C
Beam Divergence	$\theta_{\perp} \times \theta_{\parallel}$	40x8	deg
Electrical Specifications			
Slope Efficiency	E_S	≥ 0.8	W/A
Conversion Efficiency	N_S	$\geq 30\%$	
Threshold Current	I_{TH}	≤ 15	A
Operating Current	I_F	≤ 75	A
Operating Voltage	U_F	≤ 40	V
Absolute Maximum Ratings			
Reverse Voltage	U_R	2.5	V
Operating Temperature	T_{OP}	+10 ... +40	°C
Storage Temperature	T_{STG}	-40 ... +85	°C



